Abstracts

0.25/spl mu/m pHEMT 40Gb/s E/O modulator drivers

J.M. Carroll, A. Coutant, M.S. Heins, C.F. Campbell and E. Reese. "0.25/spl mu/m pHEMT 40Gb/s E/O modulator drivers." 2002 MTT-S International Microwave Symposium Digest 02.1 (2002 Vol. I [MWSYM]): 489-492 vol.1.

The development of two high voltage, 40 Gb/s E/O modulator driver ICs is described. Both were designed with a Distributed Amplifier (DA) topology utilizing a 0.25/spl mu/m GaAs pHEMT production process. The modulator drivers exhibit 6 dB of small signal gain, greater than 42 GHz of 3-dB bandwidth, and better than 6.5-V/sub pp/ output swing.

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